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FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/04/2004	Toshiharu Furukawa	BUR920040152US1	5763	
590 08/11/2006		EXAM	EXAMINER	
WOOD, HERRON & EVANS, LLP (IBM-BUR)			STARK, JARRETT J	
TOWER		ART UNIT	PAPER NUMBER	
441 VINE STREET CINCINNATI, OH 45202		2823		
	10/04/2004 590 08/11/2006 RON & EVANS, LLP (TOWER EET	Toshiharu Furukawa 590 08/11/2006 RON & EVANS, LLP (IBM-BUR) TOWER EET	10/04/2004 Toshiharu Furukawa BUR920040152US1 590 08/11/2006 EXAM RON & EVANS, LLP (IBM-BUR) TOWER EET ART UNIT	

DATE MAILED: 08/11/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)			
		10/711,764	FURUKAWA ET AL.			
	Office Action Summary	Examiner	Art Unit			
		Jarrett J. Stark	2823			
Period fo	The MAILING DATE of this communication apports. Reply	pears on the cover sheet with the c	orrespondence addre	!SS		
WHIC - Exte after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPLECTION OF THE MAILING DEPOSION OF THE MAILING	ATE OF THIS COMMUNICATION 136(a). In no event, however, may a reply be time will apply and will expire SIX (6) MONTHS from e, cause the application to become ABANDONE	N. nely filed the mailing date of this comm D (35 U.S.C. § 133).			
Status						
1)	Responsive to communication(s) filed on <u>01 A</u>	ugust 2006.				
/ 	·					
· —	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is					
,	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposit	ion of Claims					
4) 💢	4)⊠ Claim(s) <u>1-8,10-12,14-21 and 23</u> is/are pending in the application.					
·	4a) Of the above claim(s) is/are withdrawn from consideration.					
	5) Claim(s) is/are allowed.					
	6) Claim(s) 1-8, 10-12, 14-21, and 23 is/are rejected.					
7)	Claim(s) is/are objected to.					
8)	Claim(s) are subject to restriction and/o	or election requirement.				
Applicat	ion Papers					
9)	The specification is objected to by the Examine	er.				
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority (under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).						
a) All b) Some * c) None of:						
	1. Certified copies of the priority documents have been received.					
 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage 						
	application from the International Bureau (PCT Rule 17.2(a)).					
* (See the attached detailed Office action for a list		ed.			
	\					
Attachmen	et(s)					
	ce of References Cited (PTO-892)	4) Interview Summary	•			
	ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08)	Paper No(s)/Mail Da 5) Notice of Informal F	ate Patent Application (PTO-15	52)		
Paper No(s)/Mail Date 6) Other:						

DETAILED ACTION

Response to Amendment

Applicant's request for reconsideration of the finality of the rejection of the last Office action is persuasive and, therefore, the finality of that action is withdrawn. However, upon further consideration, a new ground(s) of rejection is made in view of Dahl et al. (US 2002/0130407).

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-8, 10-12, 14-21, and 23 are rejected under 35 U.S.C. 102(b) as being anticipated by <u>Dahl et al.</u> (US 2002/0130407).

Regarding claim 1, <u>Dahl</u> discloses a dielectric material for forming a structure of an integrated circuit, said dielectric material comprising:

- a plurality of fluorinated carbon nanostructures (Dahl ¶ [0074]); and
- a copolymer layer binding said fluorinated carbon nanostructures to define the dielectric material (<u>Dahl</u> ¶ [0075]).

Regarding claim 3, <u>Dahl</u> discloses the dielectric material of claim 1 wherein said fluorinated carbon nanostructures comprise a plurality of fluorinated carbon nanotubes (<u>Dahl</u> ¶ [0007]).

Regarding claim 4, <u>Dahl</u> discloses the dielectric material of claim 1 wherein said dielectric material has a dielectric constant of less than about 3 (<u>Dahl</u> ¶ [0139]).

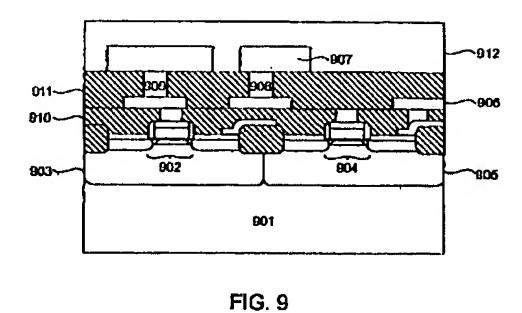
Regarding claim 5, <u>Dahl</u> discloses the dielectric material of claim 1 wherein said structure further comprises at least one conductive feature disposed in said dielectric material (<u>Dahl</u> ¶ [0135] – fluorinated carbon is conductive feature).

Regarding claim 6, <u>Dahl</u> discloses the dielectric material of claim 1 wherein said fluorinated carbon nanostructures comprise a plurality of fluorinated carbon buckyballs (<u>Dahl</u> ¶ [0007] – fullerenes are buckyballs).

Regarding claim 7, <u>Dahl</u> discloses the dielectric material of claim 1 further comprising a cap layer on said dielectric material (<u>Dahl</u> Figure 9 & ¶ [0139] – dielectric layers are [910 & 911] and capped with layers [907 & 912]).

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Regarding claim 8, <u>Dahl</u> discloses the dielectric material of claim 7 wherein said fluorinated carbon nanostructures, said copolymer layer, and said cap layer have an effective dielectric constant of less than about 3 (<u>Dahl</u> ¶ [0139]).

Regarding claim 10, <u>Dahl</u> discloses the dielectric material of claim [[7]] 1 wherein said fluorinated carbon nanostructures and said copolymer layer have an effective dielectric constant of less than about 3 (<u>Dahl</u> ¶ [0139]).

Regarding claim 11, <u>Dahl</u> discloses a semiconductor structure formed on a substrate, comprising:

a dielectric layer comprising a plurality of fluorinated carbon nanostructures and a copolymer layer binding said fluorinated carbon nanostructures(<u>Dahl</u> ¶ [0074 - 75]); and

at least one conductive feature in said dielectric layer, said at least one conductive feature electrically isolated from nearby conductive features by portions of said dielectric layer (<u>Dahl</u> Figure 9 & ¶ [0139]).

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Regarding claim 12, <u>Dahl</u> discloses the semiconductor structure of claim 11 wherein said dielectric layer has an exposed surface, and further comprising:

a cap layer of an insulating material at least partially covering said exposed surface, said cap layer having a top surface, and said conductive feature having a top surface substantially coplanar with said top surface of said cap layer (<u>Dahl</u> Figure 9 – [910 & 911] → Dielectric layer, [907] → interconnect & [912] → passivation layer).

Regarding claim 14, <u>Dahl</u> discloses the semiconductor structure of claim 11 wherein said fluorinated carbon nanostructures comprise a plurality of fluorinated carbon nanotubes (<u>Dahl</u> ¶ [0007]).

Regarding claim 15, <u>Dahl</u> discloses the semiconductor structure of claim 11 wherein said dielectric layer has a dielectric constant of less than about 3 (<u>Dahl</u> ¶ [0139]).

Regarding claim 16, <u>Dahl</u> discloses the semiconductor structure of claim 11 wherein said structure comprises a plurality of conductors electrically isolated by said layer of said dielectric material (<u>Dahl</u> Figure 9 – [910 & 911] → Dielectric layer, [907] → interconnect & [912] → passivation layer).

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Regarding claim 17, <u>Dahl</u> discloses the semiconductor structure of claim 11 wherein said fluorinated carbon nanostructures comprise a plurality of fluorinated carbon buckyballs (<u>Dahl</u> ¶ [0007] – fullerenes are buckyballs).

Regarding claim 18, <u>Dahl</u> discloses the semiconductor structure of claim 11 further comprising: a cap layer disposed on said fluorinated carbon nanostructures (<u>Dahl</u> Figure 9 – [910 & 911] → Dielectric layer, [907] → interconnect & [912] → passivation layer).

Regarding claim 19, <u>Dahl</u> discloses the semiconductor structure of claim 18 wherein said fluorinated carbon nanostructures, said copolymer layer, and said cap layer collectively have a dielectric constant of less than about 3 (<u>Dahl</u> ¶ [0139]).

Regarding claim 20, <u>Dahl</u> discloses the semiconductor structure of claim 11 further comprising:

a substrate selected from the group consisting of an interconnect level, a dielectric material, a buried barrier layer, a metallization line, and a semiconductor wafer (Dahl Figure 9 – [910 & 911] → Dielectric layer, [907] → interconnect & [912] → passivation layer).

Regarding claim 21, <u>Dahl</u> discloses the integrated circuit comprising a plurality of circuit elements and the semiconductor structure of claim 11, said at least one

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conductive feature being electrically coupled with at least one of said circuit elements (<u>Dahl</u> Figure 9 – [910 & 911] → Dielectric layer, [907] → interconnect & [912] → passivation layer).

Regarding claim 23, Dahl discloses the dielectric material of claim [[22]] 11 wherein said fluorinated carbon nanostructures and said copolymer layer have an effective dielectric constant of less than about 3 (Dahl ¶ [0139]).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Jarrett J. Stark whose telephone number is (571) 272-6005. The examiner can normally be reached on Monday - Thursday 7:00AM -5:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith can be reached on (571) 272-1907. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

JJS August 7, 2006

MICHELLE ESTRADA
PRIMARY EXAMINER